2SK1214

Silicon N-channel Power F-MOS FET

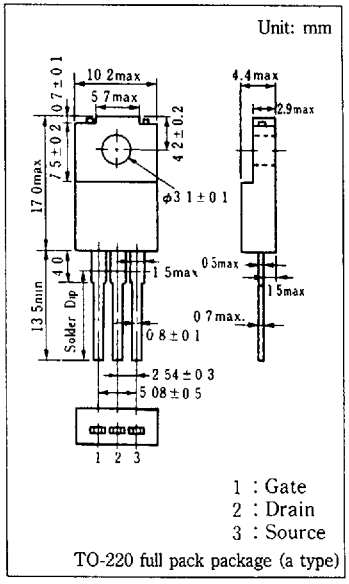
■ Features

- Low ON resistance R_{DS} (on) : R_{DS} (on) 1 = 0.06Ω (typ.)
- High switching rate : t_f = 110ns (typ.)
- No secondary breakdown
- Low voltage drive is possible (V_{GS} = 4V).

■ Application

- DC-DC converter
- No contact relay
- Solenoid drive
- Motor drive

■ Package Dimensions



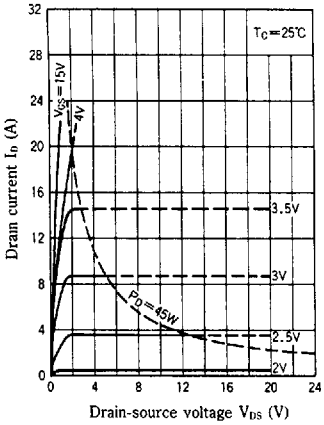
■ Absolute Maximum Ratings (Tc=25°C)

Item		Symbol	Value	Unit
Drain-source voltage		V_{DSS}	80	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	At 4V driving	I_D	12	A
	DC	I_D	20	
	Peak to-peak value	I_{DP}	40	
Power dissipation	Tc=25℃	P_D	45	W
	Ta=25℃		2.0	
Channel temperature		T_{ch}	150	℃
Storage temperature		T_{stg}	−55~+150	℃

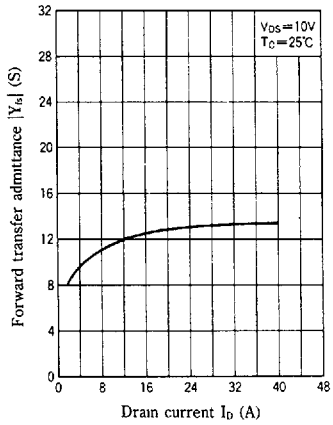
■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Drain current	I_{DSS}	V_{DS}=65V, V_{GS}=0			10	μA
Gate-source current	I_{GSS}	V_{GS}=±20V, V_{DS}=0			±1	μA
Drain-source voltage	V_{DSS}	I_D= 1 mA, V_{GS}=0	80			V
Gate threshold voltage	V_{th}	V_{DS}=10V, I_D=1mA	1		2.5	V
Drain-source ON resistance	R_{DS}(on)1	V_{GS}=10V, I_D=6A		0.06	0.09	Ω
Drain-source ON resistance	R_{DS}(on)2	V_{GS}=4V, I_D=6A		0.09	0.135	Ω
Forward transfer admittance	| Yfs |	V_{DS}=10V, I_D=6A	6	10		S
Input capacitance	C_{iss}	V_{DS}=10V, V_{GS}=0, f=1MHz		1450		pF
Output capacitance	C_{oss}			550		pF
Reverse transfer capacitance	C_{rss}			190		pF
Turn-on time	t_{on}	V_{GS}=10V, I_D=6A, V_{DD}≒30V, R_L=5Ω		60		ns
Fall time	t_f			110		ns
Delay time	t_d(off)			330		ns

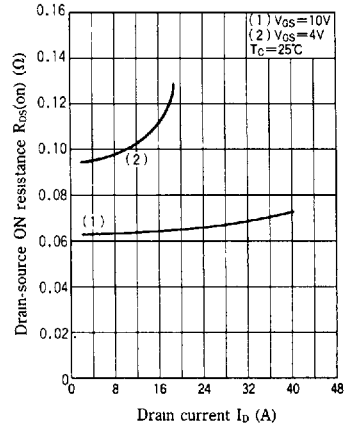
$I_D - V_{DS}$



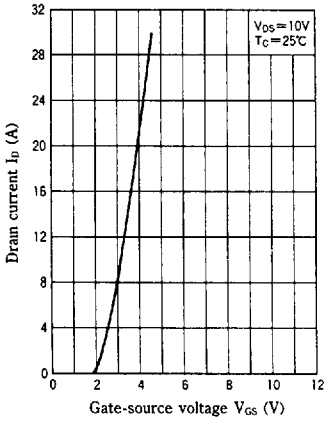
$|Y_{fs}| - I_D$



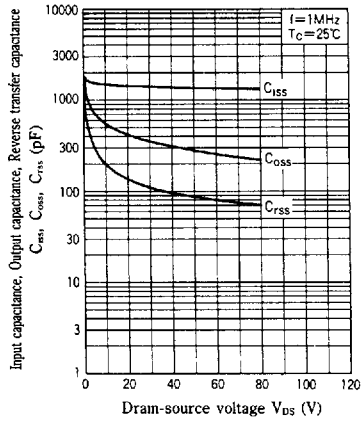
$R_{DS}(on) - I_D$



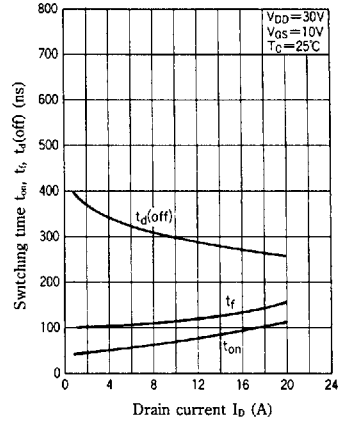
$I_D - V_{GS}$



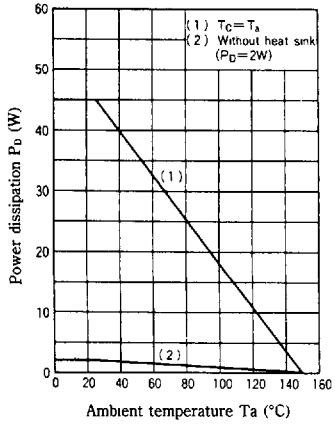
$C_{iss}, C_{oss}, C_{rss} - V_{DS}$



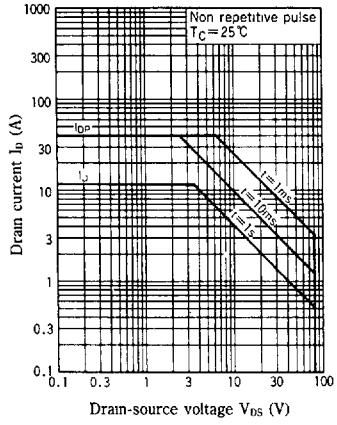
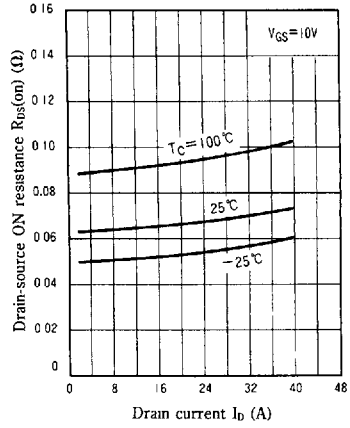
$t_{on}, t_f, t_d(off) - I_D$



$P_D - Ta$



Safety operation area (ASO)



$R_{DS}(on) - I_D$